

# PUMD17-Q

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

13 June 2025

Product data sheet

## 1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH17-Q PNP/PNP complement: PUMB17-Q

### 2. Features and benefits

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- · Reduces pick and place cost
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replacement of general-purpose transistors in digital applications

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	33	47	61	kΩ
R2/R1	bias resistor ratio		[2]	0.37	0.47	0.57	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



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## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	D. D. D.	
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2
				006aaa143

## 6. Marking

Table 3. Marking codes

Type number	Marking code[1]
PUMD17-Q	D9%

[1] % = placeholder for manufacturing site code

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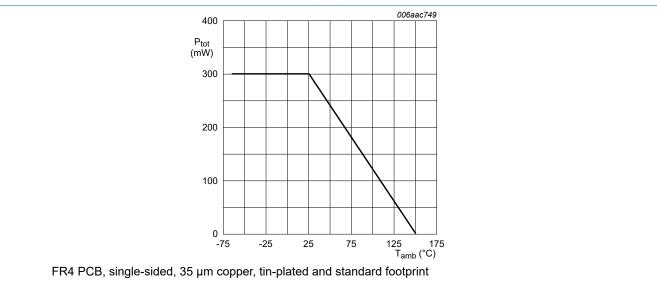
## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or			'		
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	[1]	-	10	V
VI	input voltage	TR1		-10	40	V
		TR2		-40	10	V
Io	output current		[1]	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	200	mW
Per device			'			'
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

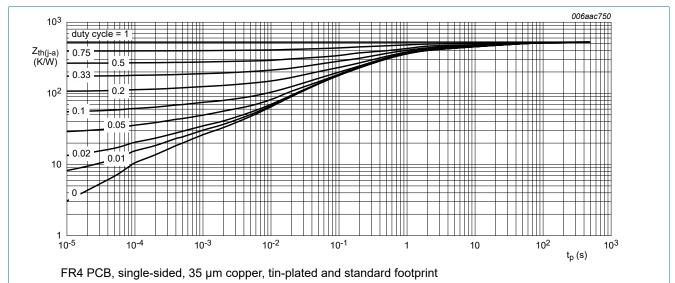


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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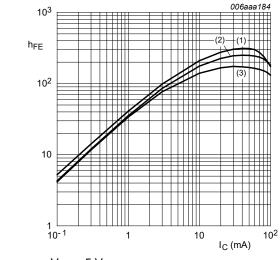
## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	= 2 mA; $I_B$ = 0 A; $T_{amb}$ = 25 °C [1		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	[1]	-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	110	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C	[1]	60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	-	1.7	1.2	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C	[1]	4	2.7	-	V
R1	bias resistor 1 (input)		[2]	33	47	61	kΩ
R2/R1	bias resistor ratio		[2]	0.37	0.47	0.57	
TR1 (NPN)							
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
TR2 (PNP)			•				
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF

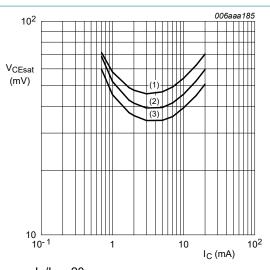
For the PNP transistor with negative polarity. See section "Test information" for resistor calculation and test conditions.

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$



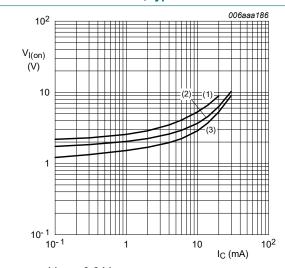
V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



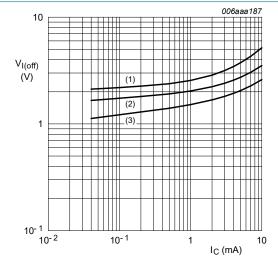
 $V_{CE} = 0.3 V$ 

(1) T<sub>amb</sub> = -40 °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

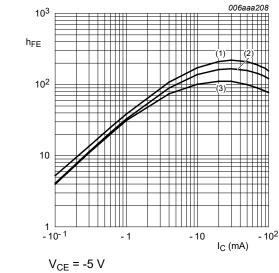
(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

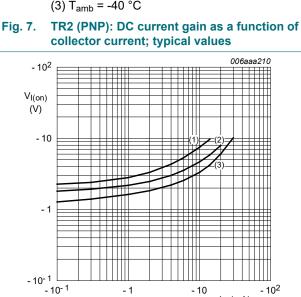
TR1 (NPN): Off-state input voltage as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$



(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

collector current; typical values



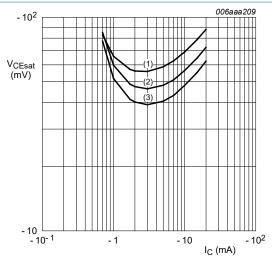
 $V_{CE} = -0.3 \text{ V}$ (1) T<sub>amb</sub> = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 100 °C

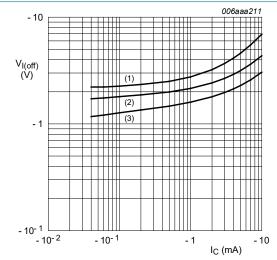
Fig. 9. of collector current; typical values

I<sub>C</sub> (mA)



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE}$  = -5 V

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

## 10. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

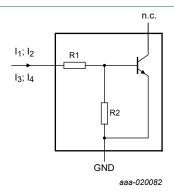


Fig. 11. NPN transistor: Resistor test circuit

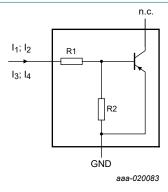


Fig. 12. PNP transistor: Resistor test circuit

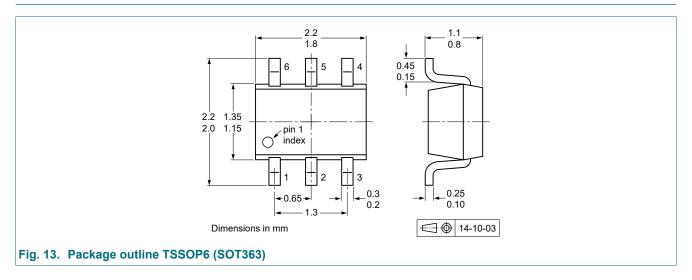
### **Resistor test conditions**

Table 7. Resistor test conditions

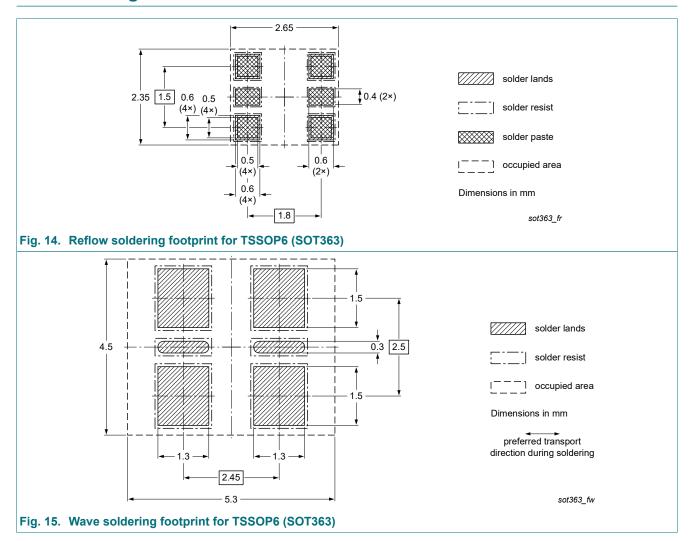
PUMD17-Q	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14	
TR1 (NPN)	47	22	55 μΑ	105 μΑ	-55 μΑ	-105 μA	
TR2 (PNP)	47	22	-55 μA	-105 μA	55 µA	105 μΑ	

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

## 11. Package outline



## 12. Soldering



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## 13. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD17-Q v.1	20250613	Product data sheet	-	-

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$

## 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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